

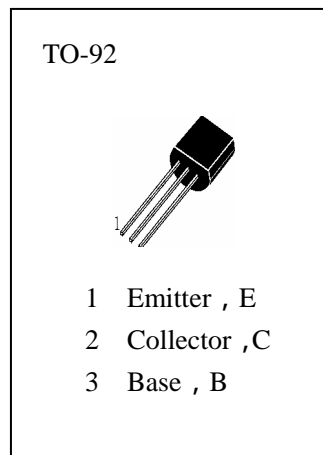


APPLICATIONS

The H945 is designed for driver stage of AF amplifier
And low speed switching.

ABSOLUTE MAXIMUM RATINGS (Ta=25)

- T_{stg}—Storage Temperature..... -55~150
- T_j—Junction Temperature.....150
- P_C—Collector Dissipation.....250mW
- V_{CBO}—Collector-Base Voltage.....60V
- V_{CEO}—Collector-Emitter Voltage.....50V
- V_{EBO}—Emitter-Base Voltage.....5V
- I_C—Collector Current.....150mA



ELECTRICAL CHARACTERISTICS (Ta=25)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	60			V	I _C =100 μ A, I _E =0
BVCEO	Collector-Emitter Breakdown Voltage	50			V	I _C =100 μ A, I _B =0
BVEBO	Emitter-Base Breakdown Voltage	5			V	I _E =100 μ A, I _C =0
HFE	DC Current Gain	90		600		V _{CE} =6V, I _C =1mA
VCE(sat)	Collector- Emitter Saturation Voltage			0.3	V	I _C =100mA, I _B =10mA
VBE(sat)	Base-Emitter Saturation Voltage			1.0	V	I _C =100mA, I _B =10mA
ICBO	Collector Cut-off Current			100	nA	V _{CB} =60V, I _E =0
IEBO	Emitter Cut-off Current			100	nA	V _{EB} =5V, I _C =0
f _T	Current Gain-Bandwidth Product		250		MHZ	V _{CE} =6V, I _C =10mA
Cob	Output Capacitance		3.0		pF	V _{CB} =6V, I _E =0, f=1MHZ
NF	Noise Figure		4.0		dB	V _{CE} =6V, I _C =0.5mA, f=1KHZ, RS=500

hFE Classification

R	Q	P	K
90—180	135—270	200—400	300—600

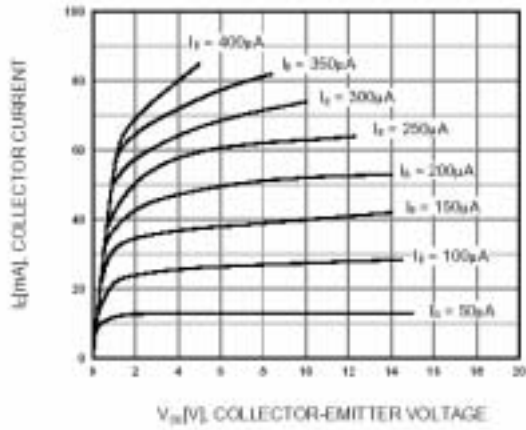


Figure 1. Static Characteristic

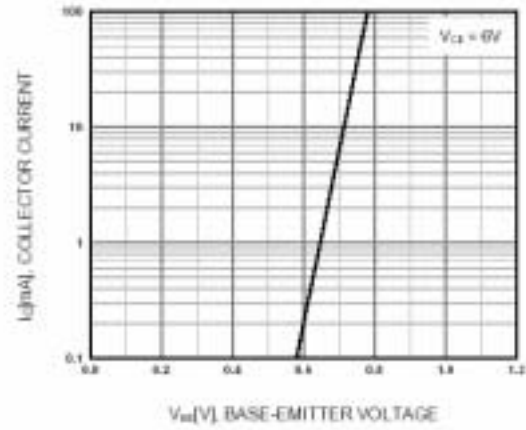


Figure 2. Transfer Characteristic

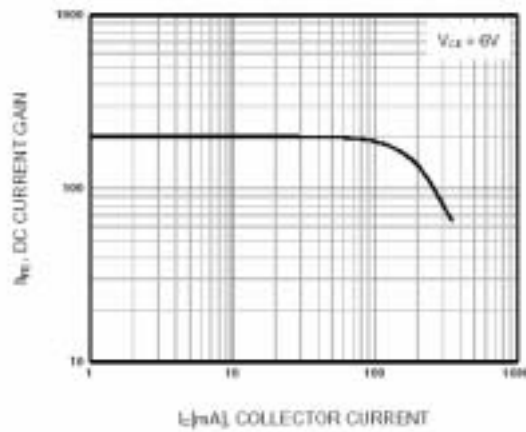


Figure 3. DC current Gain

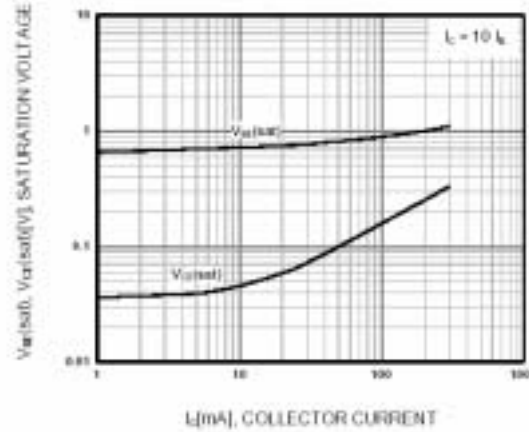


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

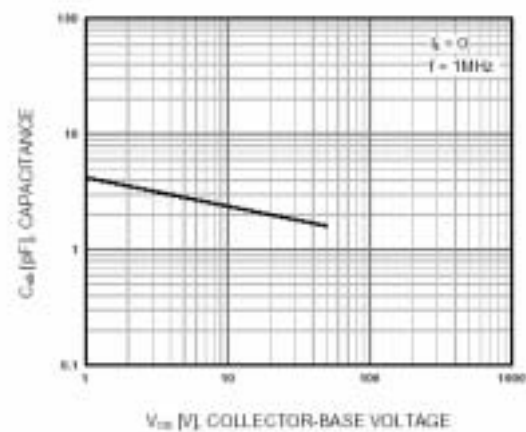


Figure 5. Output Capacitance

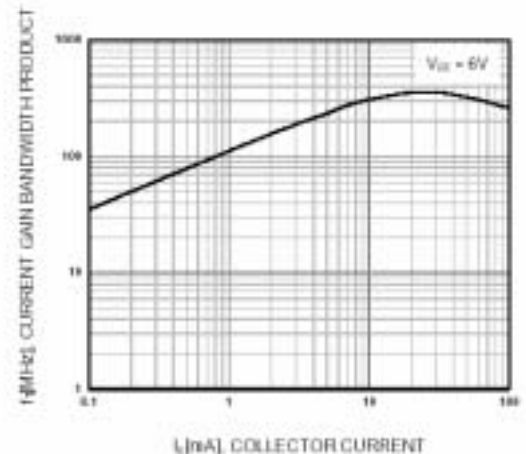


Figure 6. Current Gain Bandwidth Product